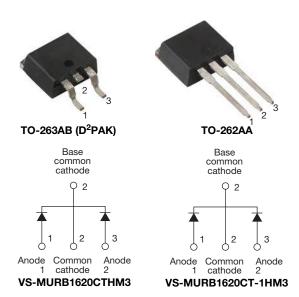


VS-MURB1620CTHM3, VS-MURB1620CT-1HM3

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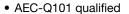
Ultrafast Rectifier, 2 x 8 A FRED Pt®



PRODUCT SUMMARY	
Package	TO-263AB (D ² PAK), TO-262AA
I _{F(AV)}	2 x 8 A
V_{R}	200 V
V _F at I _F	0.895 V
t _{rr} (typ)	19 ns
T _J max.	175 °C
Diode variation	Common cathode

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C



- Meets JESD 201 class 1 whisker test
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Peak repetitive reverse voltage		V_{RRM}		200	V	
Average rectified forward current per leg		1		8.0		
Average rectified forward current	total device	I _{F(AV)}	Rated V _R , T _C = 150 °C	16	Α	
Non-repetitive peak surge current per leg		I_{FSM}		100	A	
Peak repetitive forward current per leg		I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	16		
Operating junction and storage temp	eratures	T_J , T_{Stg}		-65 to +175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	200	-	-		
Forward voltage		I _F = 8 A	-	-	0.975	V	
	V_{F}	I _F = 8 A, T _J = 150 °C	-	-	0.895		
		$V_R = V_R$ rated	-	-	5		
Reverse leakage current	1_	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	ı	-	250	μA	
neverse leakage current	I _R	$V_{R} = 200 \text{ V}$	ı	25	-	μΑ	
Junction capacitance	C _T	Measured lead to lead 5 mm from package body	-	8.0	-	pF	
Series inductance	L _S	$I_{R} = 100 \ \mu A$	200	-	_	nH	

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		I _F = 1.0 A, dI _F /dt = 1	00 A/μs, V _R = 30 V	-	19	-	
Reverse recovery time	t _{rr}	T _J = 25 °C		-	20	-	ns
		T _J = 125 °C		-	34	-	
Deals were suggested		T _J = 25 °C	I _F = 8 A	-	1.7	-	^
Peak recovery current	I _{RRM}	T _J = 125 °C	dl _F /dt = 200 A/μs V _R = 160 V	-	4.2	-	Α
Reverse recovery charge	0	T _J = 25 °C	''	-	23	-	nC
	Q _{rr}	T _J = 125 °C		-	75	-	IIC

THERMAL - MECHANIC	CAL SPEC	IFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C
Thermal resistance, junction to case per leg	R_{thJC}		-	-	3.0	
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	50	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Maight			-	2.0	-	g
Weight			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Maulina davias		Case style TO-263AB (D ² PAK)	MURB1620CTH			
Marking device		Case style TO-262AA		MURB16	20CT-1H	

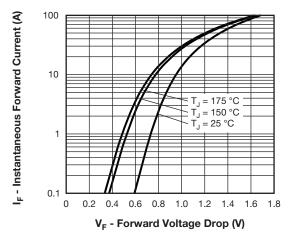


Fig. 1 - Typical Forward Voltage Drop Characteristics

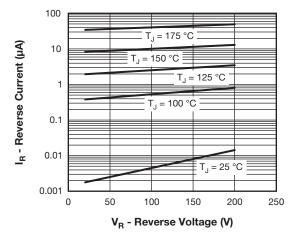


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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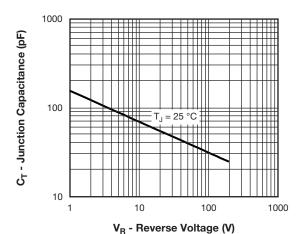


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

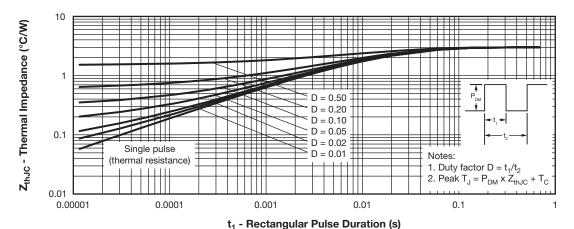


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

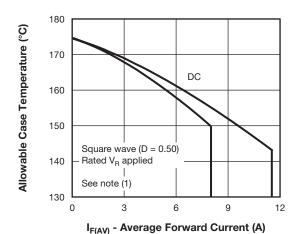


Fig. 5 - Maximum Allowable Case Temperature vs.
Average Forward Current

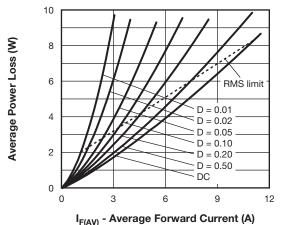


Fig. 6 - Forward Power Loss Characteristics

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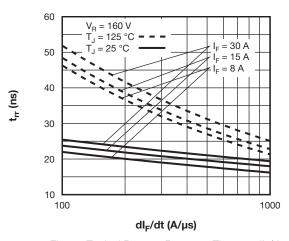


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

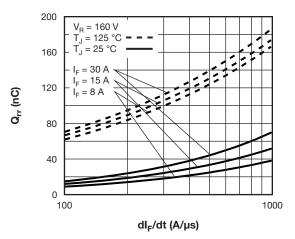
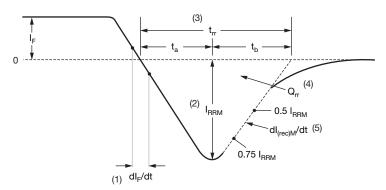


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \text{ (1 - D); } I_R \text{ at } V_{R1} = \text{Rated } V_R \\ \end{array}$



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{r}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

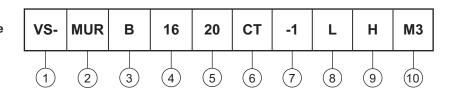
Fig. 9 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Ultrafast MUR series

3 - $B = D^2PAK/TO-262$

4 - Current rating (16 = 16 A)

5 - Voltage rating (20 = 200 V)

6 - CT = center tap (dual)

7 - • None = D²PAK

• -1 = TO-262

8 - • None = tube (50 pieces)

• L = tape and reel (left oriented, for D²PAK package)

• R = tape and reel (right oriented, for D²PAK package)

9 - H = AEC-Q101 qualified

10 - Environmental digit:

• M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-MURB1620CTHM3	50	1000	Antistatic plastic tube					
VS-MURB1620CT-1HM3	50	1000	Antistatic plastic tube					
VS-MURB1620CTLHM3	800	800	13" diameter reel					
VS-MURB1620CTRHM3	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS						
Dimensions	TO-263AB (D ² PAK)	www.vishay.com/doc?95046				
Dimensions	TO-262AA	www.vishay.com/doc?95419				
De describer de la constitución	TO-263AB (D ² PAK)	www.vishay.com/doc?95444				
Part marking information	TO-262AA	www.vishay.com/doc?95443				
Packaging information	TO-263AB (D ² PAK)	www.vishay.com/doc?95032				



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D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INC	HES	NOTES		SYMBOL		ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOIES	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

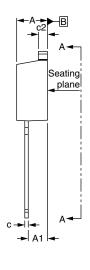
- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB

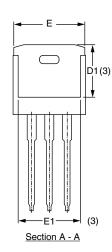


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TO-262

DIMENSIONS in millimeters and inches



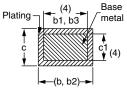


⊕ 0.010**⋒**|A**⋒**|B

Lead assignments



<u>Diodes</u>
1. - Anode (two die)/open (one die)
2., 4. - Cathode
3. - Anode



Section B - B and C - C Scale: None

CYMPOL	MILLIN	METERS	INC	HES	NOTES
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
Е	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100	BSC	
L	13.46	14.10	0.530	0.555	
L1	=	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- $^{(3)}$ Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Controlling dimension: inches
- (6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline



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